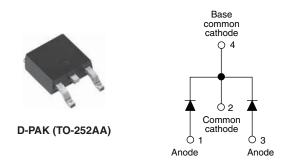
**Vishay Semiconductors** 



### Ultrafast Rectifier, 2 x 3 A FRED Pt<sup>®</sup>



PRODUCT SUMMARY					
Package	D-PAK (TO-252AA)				
I <sub>F(AV)</sub>	2 x 3 A				
V <sub>R</sub>	200 V				
V <sub>F</sub> at I <sub>F</sub>	1.0 V				
t <sub>rr</sub> typ.	See Recovery table				
T <sub>J</sub> max.	175 °C				
Diode variation	Common cathode				

#### FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION/APPLICATIONS**

VS-MURD620CTHM3 is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V	
Average rectified forward current per device	I <sub>F(AV)</sub>	Total device, rated V <sub>R</sub> , T <sub>C</sub> = 146 °C	6		
Non-repetitive peak surge current	I <sub>FSM</sub>		50	А	
Peak repetitive forward current per diode	I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 146 °C	6		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-	
		I <sub>F</sub> = 3 A	-	-	1.0	
Forward voltage V <sub>F</sub>	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	-	0.96	V	
	I <sub>F</sub> = 6 A	-	-	1.2		
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 125 °C	-	-	1.13	
Devene legiser comment		V <sub>R</sub> = V <sub>R</sub> rated	-	-	5	
Reverse leakage current	I <sub>R</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	12	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH

Revision: 21-Aug-13

Document Number: 94742

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# VS-MURD620CTHM3



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt = 50 A/µs, V <sub>R</sub>		-	20	35	ns
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$ I_F = 3 A \\ dI_F/dt = 200 A/\mu s \\ V_R = 160 V $	-	19	-	
		T <sub>J</sub> = 125 °C		-	26	-	
Peak recovery current		T <sub>J</sub> = 25 °C		-	3.1	-	А
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	4.6	-	A	
Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	30	-	nC	
	T <sub>J</sub> = 125 °C		-	60	-	IIC III	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	9.0	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	80	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	-	-	
Waight			-	0.3	-	g
Weight			-	0.01	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D-PAK		MURD	520CTH	



## VS-MURD620CTHM3

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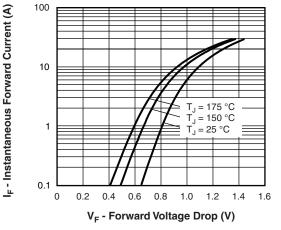
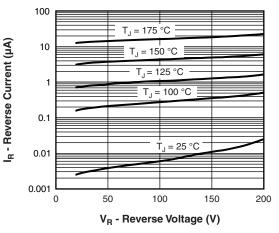
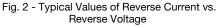


Fig. 1 - Typical Forward Voltage Drop Characteristics





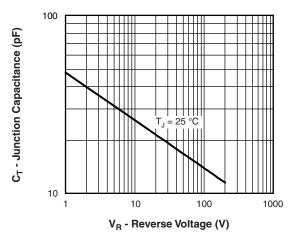


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

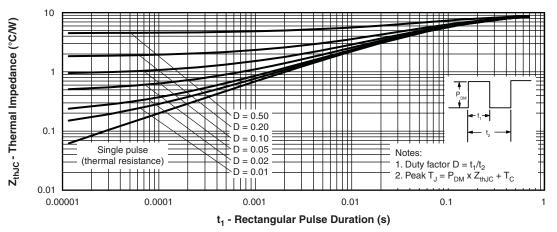


Fig. 4 - Maximum Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

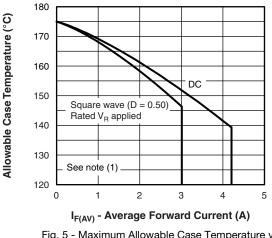
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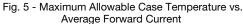
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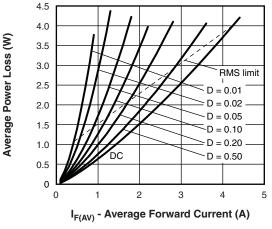


Fig. 6 - Forward Power Loss Characteristics

#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, x \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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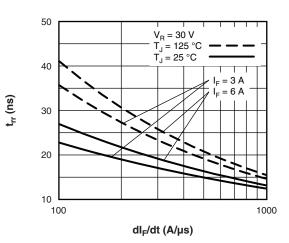


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

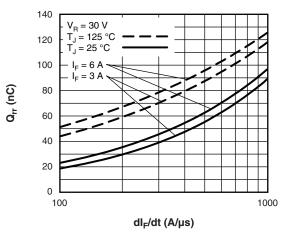


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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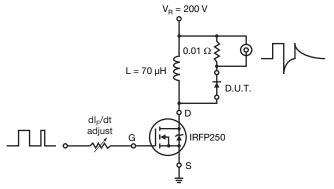


Fig. 9 - Reverse Recovery Parameter Test Circuit

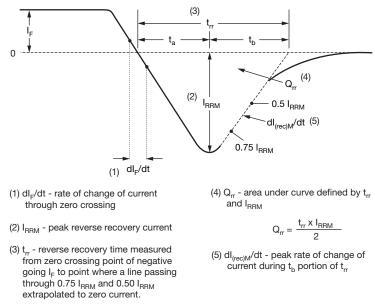
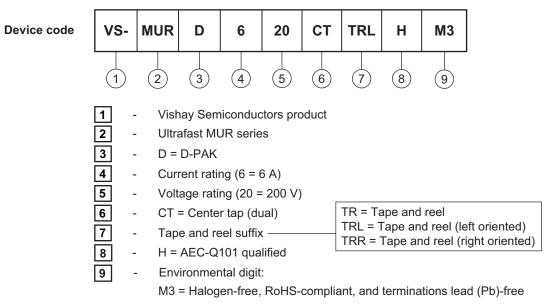


Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

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ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-MURD620CTHM3	75	3000	Antistatic plastic tube		
VS-MURD620CTTRHM3	2000	2000	13" diameter reel		
VS-MURD620CTTRLHM3	3000	3000	13" diameter reel		
VS-MURD620CTTRRHM3	3000	3000	13" diameter reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95519			
Part marking information	www.vishay.com/doc?95518			
Packaging information	www.vishay.com/doc?95033			



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